

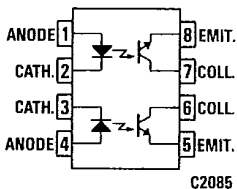
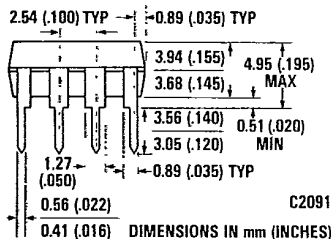
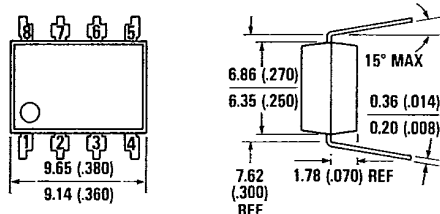
**GENERAL
INSTRUMENT**

**DUAL
PHOTOTRANSISTOR OPTOCOUPLEDERS**

Optocouplers

NEW DUALS MCT6 (20%) MCT62 (100%)
MCT61 (50%) MCT66 (6%)

PACKAGE DIMENSIONS



Equivalent Circuit

DESCRIPTION

The MCT6X optoisolators have two channels for high density applications. For four channel applications, two-packages fit into a standard 16-pin DIP socket. Each channel is an NPN silicon planar phototransistor optically coupled to a gallium arsenide infrared emitting diode.

FEATURES

- Two isolated channels per package
- Two packages fit into a 16 lead DIP socket
- 2500 volt isolation
- Choice of 4 current transfer ratios
- Underwriters Laboratory (U.L.) recognized File E50151

APPLICATIONS

- AC Line/Digital Logic — Isolate high voltage transients
- Digital Logic/Digital Logic — Eliminate spurious grounds
- Digital Logic/AC Triac Control — Isolate high voltage transients
- Twisted pair line receiver — Eliminate ground loop feedthrough
- Telephone/Telegraph line receiver — Isolate high voltage transients
- High Frequency Power Supply Feedback Control — Maintain floating ground
- Relay contact monitor — Isolate floating grounds and transients
- Power Supply Monitor — Isolate transients

ABSOLUTE MAXIMUM RATINGS

Storage Temperature -55°C to 150°C
Operating Temperature -55°C to 100°C
Lead Temperature (soldering, 10 sec.) 250°C

INPUT DIODE (each channel)

Forward current 60mA
Reverse voltage 3.0V
Peak forward current (1μs pulse, 300 pps) 3A

TOTAL INPUT

Power dissipation at 25°C ambient 100mW
Derate linearly from 25°C 1.3mW/°C

OUTPUT TRANSISTOR (each channel)

Power dissipation @ 25°C ambient 150mW
Derate linearly from 25°C 2mW/°C
Collector Current 30mA

COUPLED

Input to output breakdown voltage . . 2500 volts V_{RMS}
Total package power dissipation
@ 25°C ambient 400mW
Derate linearly from 25°C 5.33mW/°C

MCT6 MCT61 MCT62 MCT66**ELECTRO-OPTICAL CHARACTERISTICS (25° C Free Air Temperature Unless Otherwise Specified)**

CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE					
Rated forward voltage V_F		1.25	1.50	V	$I_F = 20\text{mA}$
Reverse voltage V_R	3.0	25		V	$I_R = 10\mu\text{A}$
Reverse current I_R		.001	10	μA	$V_R = 3.0\text{V}$
Junction capacitance C_j		50		pF	$V_F = 0\text{V}$
OUTPUT TRANSISTOR ($I_F = 0$)					
Breakdown voltage, collector to emitter BV_{CEO}	30	85		V	$I_C = 1.0\text{mA}$
Breakdown voltage, emitter to collector BV_{ECO}	6	13		V	$I_E = 100\mu\text{A}$
Leakage current, collector to emitter I_{CEO}		5	100	nA	$V_{CE} = 10\text{V}$
Capacitance collector to emitter C_{CE}		8		pF	$V_{CE} = 0\text{V}$
COUPLED					
DC current transfer ratio (I_C/I_F) = CTR				%	$V_{CE} = 10\text{V}$, $I_F = 10\text{mA}$
MCT6	20			%	$V_{CE} = 5\text{V}$, $I_F = 5\text{mA}$
MCT61	50			%	$V_{CE} = 5\text{V}$, $I_F = 5\text{mA}$
MCT62	100			%	$V_{CE} = 10\text{V}$, $I_F = 10\text{mA}$
MCT66	6			%	$t = 1\text{ minute}$
Isolation voltage $BV_{(I-O)}$	2500			V _{RMS}	
Isolation resistance				Ω	$V_{I-O} = 500\text{VDC}$
MCT6X— $R_{(I-O)}$	10^{11}	10^{12}		Ω	
Breakdown voltage — channel-to-channel MCT6X		500		VDC	Relative humidity = 40%
					$f = 1\text{MHz}$
Capacitance between channels		0.4		pF	
Saturation voltage — collector to emitter $V_{CE(SAT)}$				V	$I_C = 2\text{mA}$, $I_F = 16\text{mA}$
MCT6, 61, 62		0.2	0.4	V	$I_C = 2\text{mA}$, $I_F = 40\text{mA}$
MCT66		0.2	0.4	V	$I_C = 2\text{mA}$, $V_{CC} = 10\text{V}$, $R_L = 100\Omega$
Bandwidth B_W		150		kHz	
SWITCHING TIMES, OUTPUT TRANSISTOR					
Non-saturated rise time, fall time (Note 3)		2.4		μs	$I_C = 2\text{mA}$, $V_{CE} = 10\text{V}$, $R_L = 100\Omega$
Non-saturated rise time, fall time (Note 3)		15		μs	$I_C = 2\text{mA}$, $V_{CE} = 10\text{V}$, $R_L = 1\text{K}\Omega$
Saturated turn-on time (from 5.0V to 0.8V)		5		μs	$R_L = 2\text{K}\Omega$, $I_F = 40\text{mA}$
Saturated turn-off time (from saturation to 2.0V)		25		μs	$R_L = 2\text{K}\Omega$, $I_F = 40\text{mA}$

MCT6 TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES

(25° C Free Air Temperature Unless Otherwise Specified)

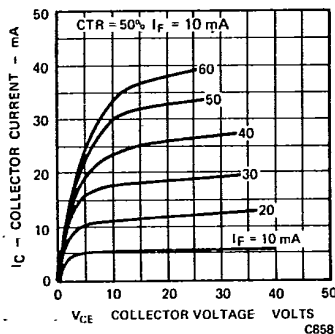


Fig. 1. I-V Curve of Phototransistor

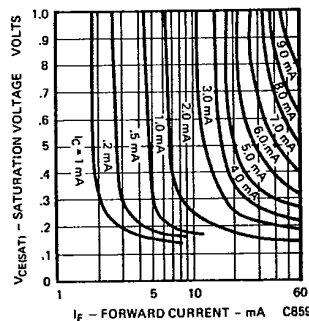


Fig. 2. I-V Curve in Saturation

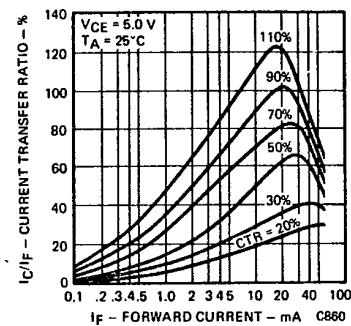


Fig. 3. CTR vs. Forward Current

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MCT6 MCT61 MCT62 MCT66

88D 03021 DT-41-83

MCT6 TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES (Cont'd)

(25°C Free Air Temperature Unless Otherwise Specified)

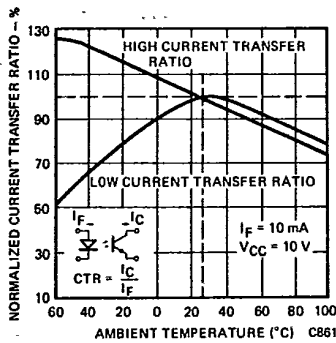


Fig. 4. Current Transfer Ratio vs. Temperature

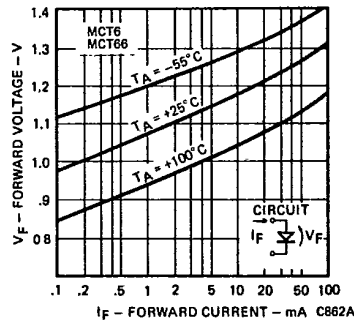


Fig. 5. I-V Curve of LED vs. Temperature

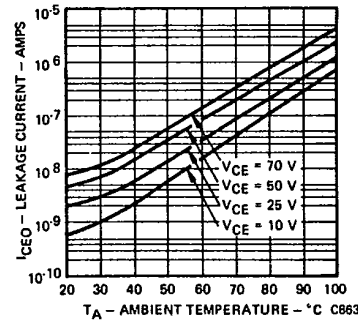


Fig. 6. Leakage Current vs. Temperature vs. Collector Voltage

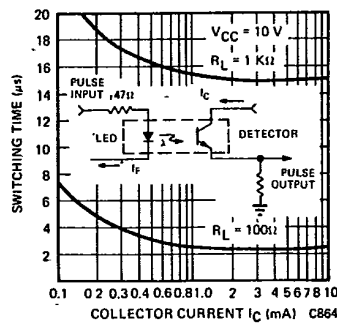


Fig. 7. Switching Time vs. Collector Current

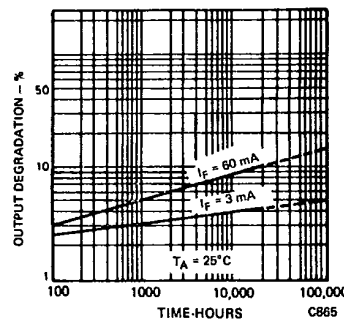


Fig. 8. Lifetime vs. Forward Current (Note 1)

MCT66 TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES

(25°C Free Air Temperature Unless Otherwise Specified)

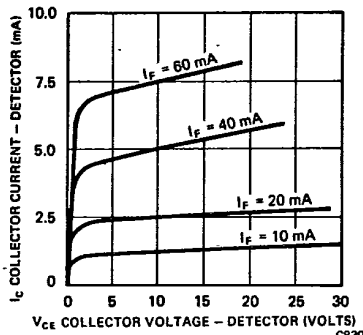


Fig. 1. Detector Output Characteristics

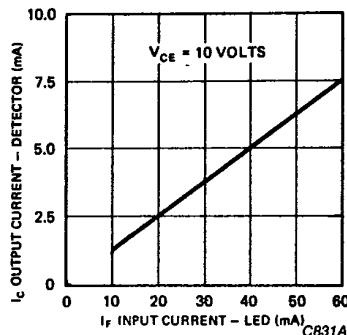


Fig. 2. Input Current vs. Output Current

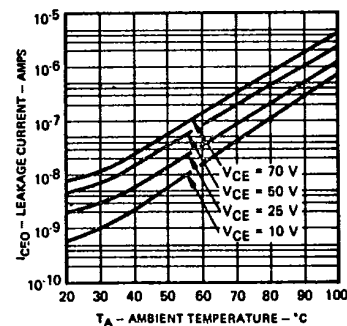


Fig. 3. Leakage Current vs. Temperature vs. Collector Voltage

Optocouplers

MCT6 MCT61 MCT62 MCT66**MCT66 TYPICAL ELECTRO-OPTICAL CHARACTERISTIC CURVES (Cont'd)**

(25°C Free Air Temperature Unless Otherwise Specified)

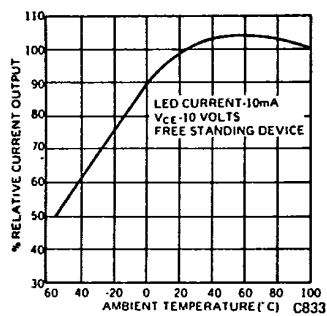


Fig. 4. Current Output vs. Temperature

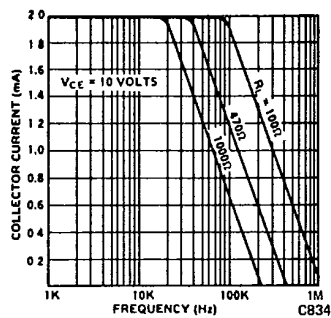


Fig. 5. Output vs. Frequency

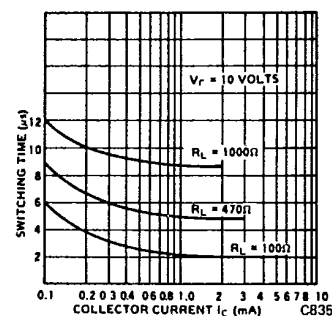


Fig. 6. Switching Time vs. Collector Current

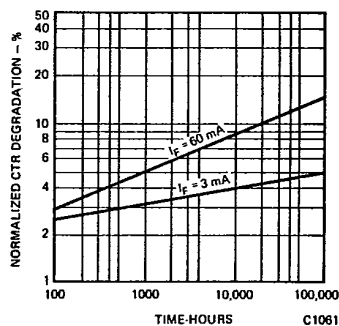
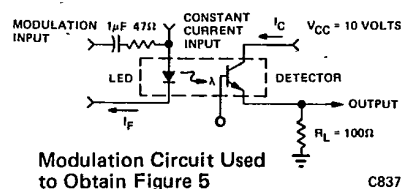
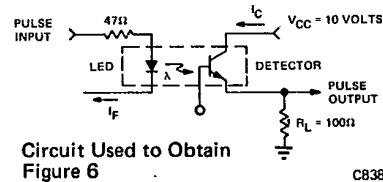


Fig. 7. Lifetime vs. Forward Current



Modulation Circuit Used to Obtain Figure 5



Circuit Used to Obtain Figure 6

NOTES

1. Normalized CTR degradation = $\frac{CTR_0 - CTR}{CTR_0}$
2. The current transfer ratio (I_C/I_F) is the ratio of the detector collector current to the LED input current with V_{CE} at 10 volts.
3. The frequency at which I_C is 3 dB down from the 1 kHz value.
4. Rise time (t_r) is the time required for the collector current to increase from 10% of its final value to 90%.
Fall time (t_f) is the time required for the collector current to decrease from 90% of its initial value to 10%.